

### **30V Dual P-Channel Enhancement Mode MOSFET**

Voltage

-30 V

Current

-7A

#### **Features**

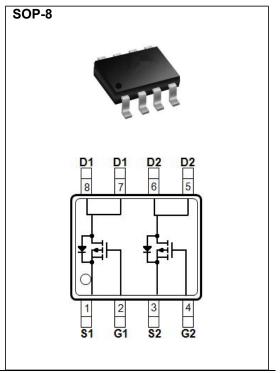
- $R_{DS(ON)}$ ,  $V_{GS}$ @-10V, $I_{D}$ @-7A<21m $\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}$ @-4.5V, $I_{D}$ @-5A<27 $m\Omega$
- · High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance

#### **Mechanical Data**

• Case: SOP-8 package

• Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0029 ounces, 0.083 grams



# Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

| PARAME   | SYMBOL               | LIMIT            | UNITS       |      |  |
|--|----------------------|------------------|-------------|------|--|
| Drain-Source Voltage                                     |                      | V <sub>DS</sub>  | -30         | V    |  |
| Gate-Source Voltage                                      |                      | V <sub>GS</sub>  | <u>+</u> 20 | V    |  |
| Continuous Drain Current                                 | T <sub>A</sub> =25°C |                  | -7          | A    |  |
|  | T <sub>A</sub> =70°C | I <sub>D</sub>   | -6          |      |  |
| Pulsed Drain Current (Note 1)                            |                      | I <sub>DM</sub>  | -28         |      |  |
| Power Dissipation  | T <sub>A</sub> =25°C |                  | 1.25        | W    |  |
|  | T <sub>A</sub> =70°C | P <sub>D</sub>   | 0.8         |      |  |
| Operating Junction and Storage Temperature Range         |                      | $T_J, T_{STG}$   | -55~150     | °C   |  |
| Typical Thermal Resistance  Junction to Ambient (Note 5) |                      | R <sub>eJA</sub> | 100         | °C/W |  |



# **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

| PARAMETER                        | SYMBOL              | TEST CONDITION   | MIN. | TYP. | MAX.         | UNITS |
|----------------------------------|---------------------|--|------|------|--------------|-------|
| Static                           |                     |  |      |      |              |       |
| Drain-Source Breakdown Voltage   | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V,I <sub>D</sub> =-250uA                           | -30  | -    | -            | V     |
| Gate Threshold Voltage           | $V_{GS(th)}$        | V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250uA             | -1.0 | -1.5 | -2.5         |       |
| Drain-Source On-State Resistance | R <sub>DS(on)</sub> | V <sub>GS</sub> =-10V,I <sub>D</sub> =-7A                            | -    | 19   | 21           | mΩ    |
| Drain-Source On-State Resistance | R <sub>DS(on)</sub> | V <sub>GS</sub> =-4.5V,I <sub>D</sub> =-5A                           | -    | 24   | 27           |       |
| Zero Gate Voltage Drain Current  | I <sub>DSS</sub>    | V <sub>DS</sub> =-30V,V <sub>GS</sub> =0V                            | -    | -    | -1.0         | uA    |
| Gate-Source Leakage Current      | I <sub>GSS</sub>    | V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V                   | -    | -    | <u>+</u> 100 | nA    |
| Dynamic (Note 6)                 |                     |  |      |      |              |       |
| Total Gate Charge                | $Q_g$               | \/ _ 45\/   _ 5A   | -    | 11   | -            | nC    |
| Gate-Source Charge               | $Q_{gs}$            | $V_{DS}$ =-15V, $I_{D}$ =-5A,<br>$V_{GS}$ =-4.5V (Note 1,2)          | -    | 3.2  | -            |       |
| Gate-Drain Charge                | $Q_{gd}$            | V <sub>GS</sub> 4.5V   | -    | 3.9  | -            |       |
| Input Capacitance                | Ciss                | \\ - 45\\ \\ -0\\  | -    | 1169 | -            | pF    |
| Output Capacitance               | Coss                | V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V,<br>f=1.0MHZ              | -    | 180  | -            |       |
| Reverse Transfer Capacitance     | Crss                | I-I.UIVITZ   | -    | 132  | -            |       |
| Turn-On Delay Time               | td <sub>(on)</sub>  | \/ - 45\/  | -    | 5.9  | -            |       |
| Turn-On Rise Time                | tr                  | $V_{DS}$ =-15V, $I_{D}$ =-1A,<br>$V_{GS}$ =-10V, $R_{G}$ =6 $\Omega$ | -    | 33   | -            | ns    |
| Turn-Off Delay Time              | td <sub>(off)</sub> | (Note 1,2)   | -    | 55   | -            |       |
| Turn-Off Fall Time               | tf                  |  | -    | 34   | -            |       |
| Drain-Source Diode               |                     |  |      |      |              |       |
| Maximum Continuous Drain-Source  | l <sub>S</sub>      |  |      | -    | -7.8         | Α     |
| Diode Forward Current            | IS                  |  | _    |      |              |       |
| Diode Forward Voltage            | V <sub>SD</sub>     | I <sub>S</sub> =-1A, V <sub>GS</sub> =0V                             | -    | -0.7 | -1.0         | V     |

#### NOTES:

- 1. Pulse width<300us, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub>=25°C.
- 5. Roja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.



#### **TYPICAL CHARACTERISTIC CURVES**

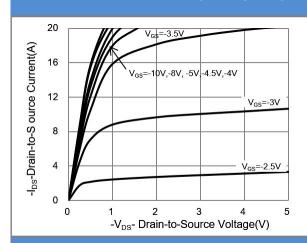
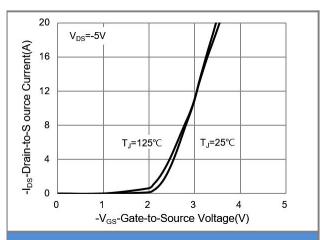


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

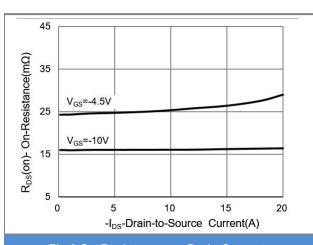


Fig.3 On-Resistance vs. Drain Current

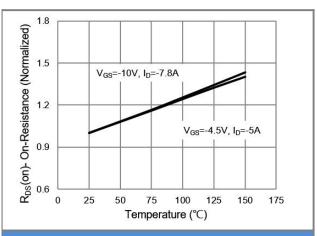


Fig.4 On-Resistance vs. Junction temperature

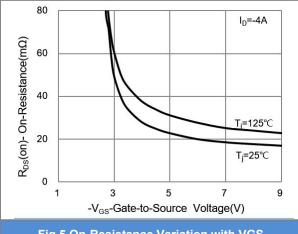
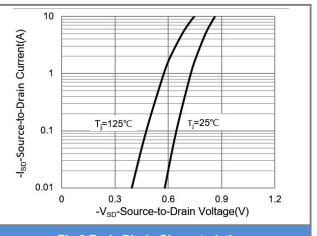


Fig.5 On-Resistance Variation with VGS.



**Fig.6 Body Diode Characteristics** 



#### **TYPICAL CHARACTERISTIC CURVES**

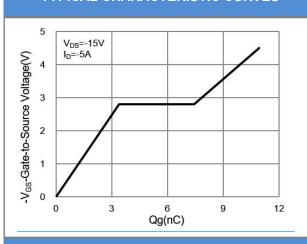


Fig.7 Gate-Charge Characteristics

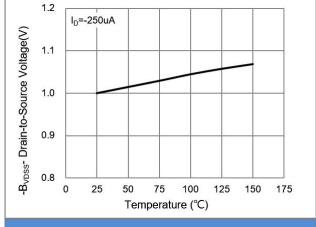


Fig.8 Breakdown Voltage Variation vs. Temperature

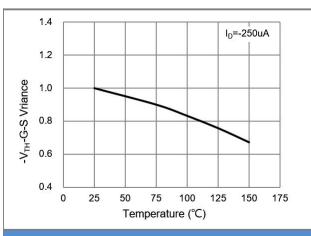


Fig.9 Threshold Voltage Variation with Temperature.

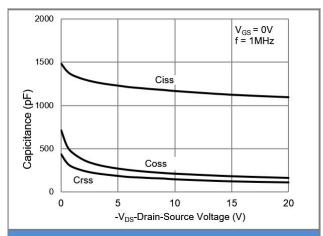


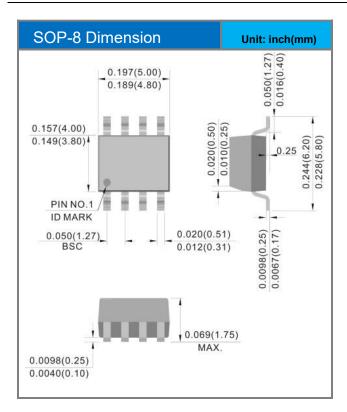
Fig.10 Capacitance vs. Drain-Source Voltage.

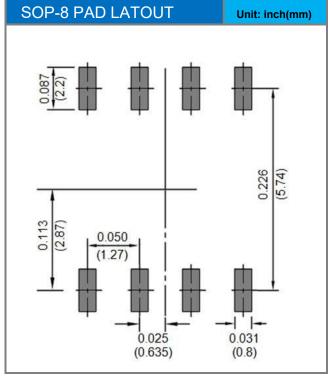


### **Part No Packing Code Version**

| Part No Packing Code | Package Type | Packing Type |
|----------------------|--------------|--------------|
| CSM4813SOP8          | SOP-8        | 3K / reel    |

## **Packaging Information & Mounting Pad Layout**







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